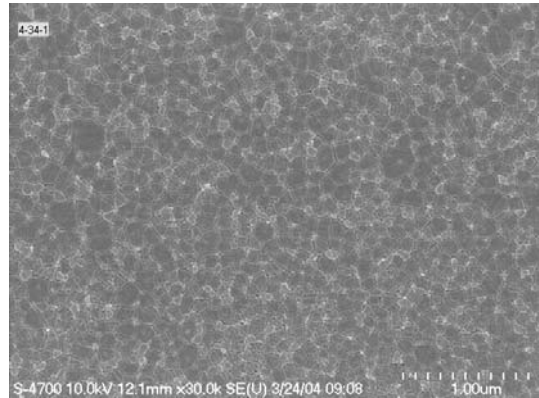
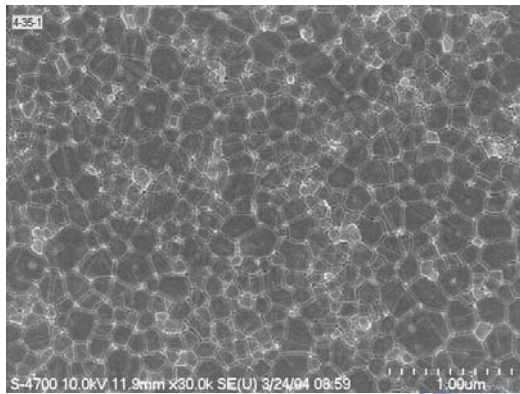


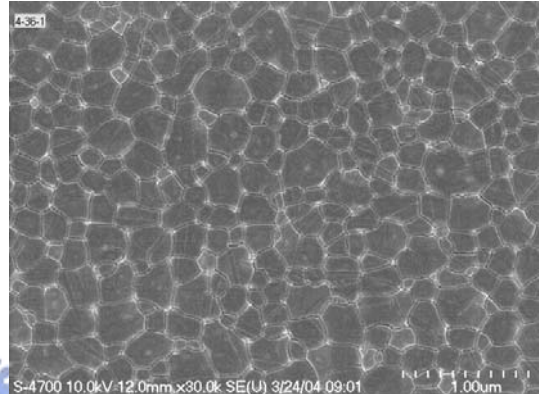
(a)



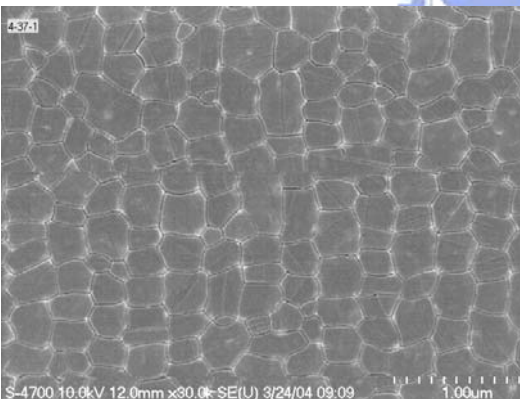
(b)



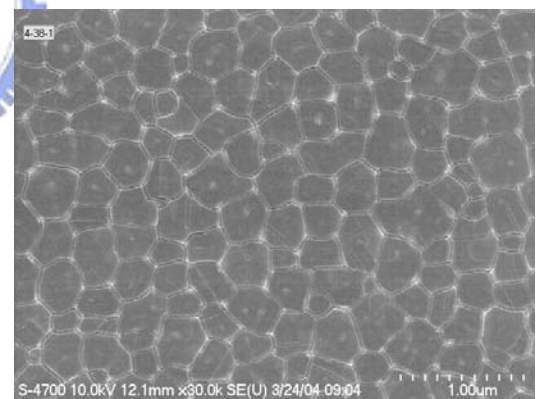
(c)



(d)

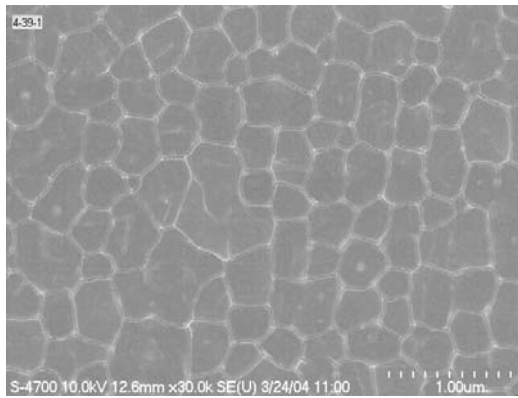


(e)

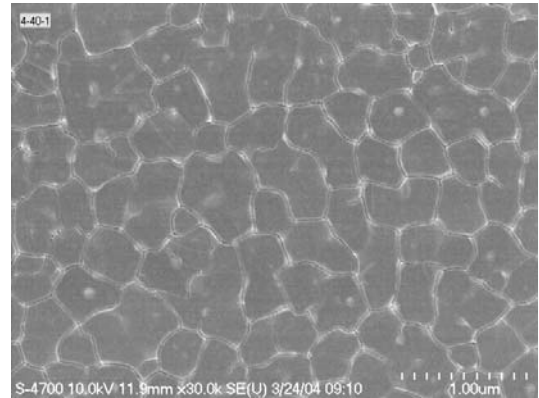


(f)

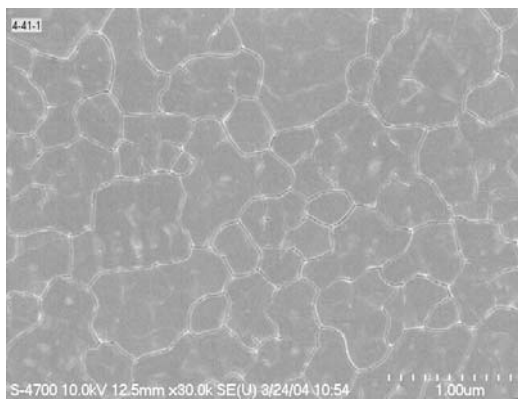
**Fig. 2-36** SEM micrographs of excimer laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The applied laser energy densities are (a) 330, (b) 340, (c) 350, (d) 360 (e) 370 (f) 380  $\text{mJ}/\text{cm}^2$ . The laser energy 950mJ, frequency 300Hz, power 285W, scan speed 6mm/sec, pitch 0.02mm, beam width 0.4mm, pre treatment clean with H<sub>2</sub>O<sub>2</sub> 30% for 420sec



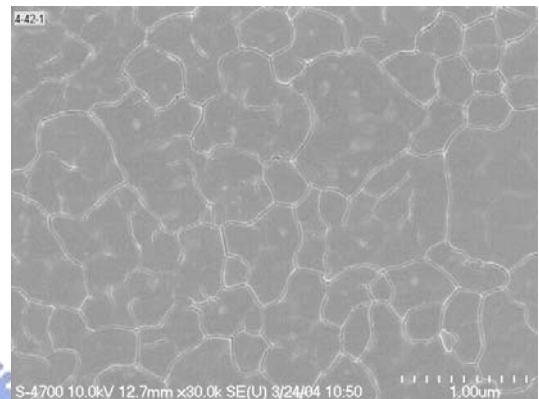
(a)



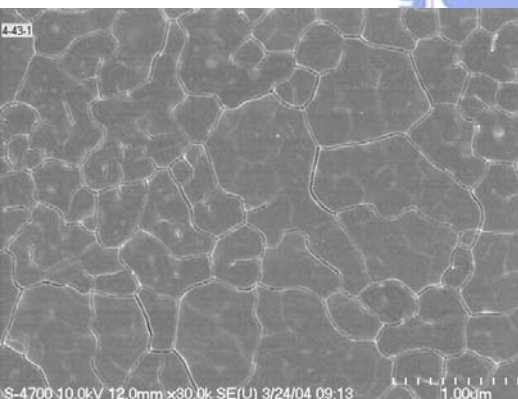
(d)



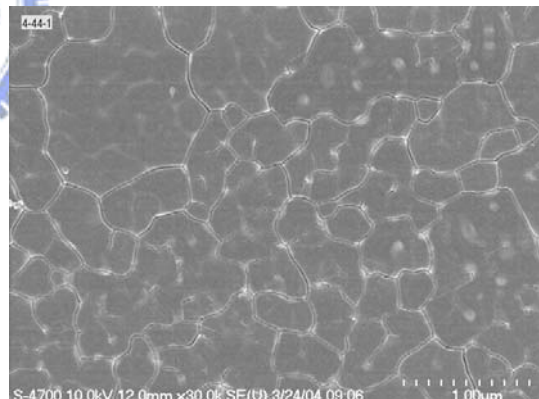
(b)



(e)



(c)



(f)

**Fig. 2-37** SEM micrographs of excimer laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The applied laser energy densities are (a) 390, (b) 400, (c) 410, (d) 420 (e) 430 (f) 440  $\text{mJ}/\text{cm}^2$ . The laser energy 950mJ, frequency 300Hz, power 285W, scan speed 6mm/sec, pitch 0.02mm, beam width 0.4mm, pre treatment clean with H<sub>2</sub>O<sub>2</sub> 30% for 420sec